

TENTATIVE TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE (U-MOSII)

TPC8106-H

LITHIUM ION BATTERY APPLICATIONS

NOTE BOOK PC, PORTABLE EQUIPMENTS APPLICATIONS

HIGH SPEED AND HIGH EFFICIENCY DC-DC CONVERTERS

INDUSTRIAL APPLICATIONS

Unit in mm

- High Speed Switching
- Small Gate Charge : $Q_g = 52 \text{ nC}$ (Typ.)
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 14 \text{ m}\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 16.6 \text{ S}$ (Typ.)
- Low Leakage Current : $I_{DSS} = -10 \mu\text{A}$ (Max.) ($V_{DS} = -30 \text{ V}$)
- Enhancement-Mode : $V_{th} = -0.8 \sim -2.0 \text{ V}$
($V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	-30	V
Drain-Gate Voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	-30	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	-10	A
	Pulse	I_{DP}	-40	A
Drain Power Dissipation ($T_a = 25^\circ\text{C}$)		P_D	2.4	W
Single Pulse Avalanche Energy**		E_{AS}	130	mJ
Avalanche Current		I_{AR}	-10	A
Repetitive Avalanche Energy*		E_{AR}	0.24	mJ
Channel Temperature		T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

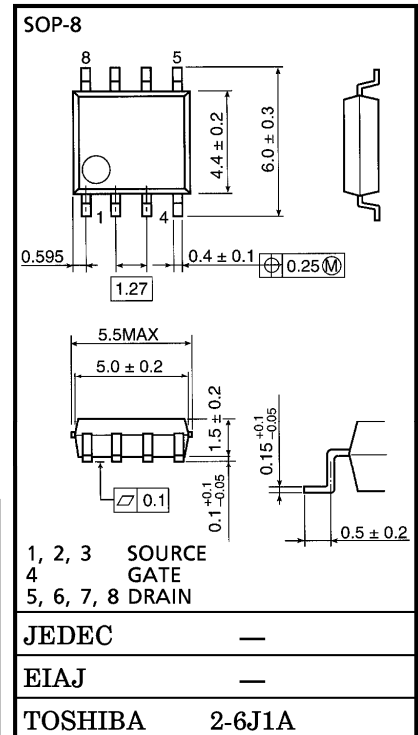
CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	52.1	$^\circ\text{C/W}$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. Junction Temperature.

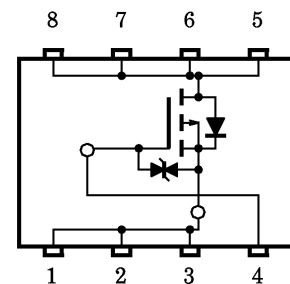
** $V_{DD} = -24 \text{ V}$, Starting $T_{ch} = 25^\circ\text{C}$, $L = 1.0 \text{ mH}$, $R_G = 25 \Omega$, $I_{AR} = -10 \text{ A}$

This transistor is an electrostatic sensitive device. Please handle with caution.



Weight : 0.08 g

CIRCUIT CONFIGURATION



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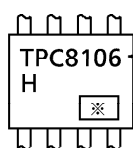
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain Cut-Off Current		I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$	—	—	-10	μA
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = -10\text{ mA}, V_{GS} = 0\text{ V}$	-30	—	—	V
		$V_{(BR)DSX}$	$I_D = -10\text{ mA}, V_{GS} = 20\text{ V}$	-15	—	—	
Gate Threshold Voltage		V_{th}	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$	-0.8	—	-2.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = -4\text{ V}, I_D = -5\text{ A}$	—	24	30	m Ω
		$R_{DS(ON)}$	$V_{GS} = -10\text{ V}, I_D = -5\text{ A}$	—	14	20	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = -10\text{ V}, I_D = -5\text{ A}$	8.3	16.6	—	S
Input Capacitance		C_{iss}	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$	—	2160	—	pF
Reverse Transfer Capacitance		C_{rss}		—	530	—	
Output Capacitance		C_{oss}		—	720	—	
Switching Time	Rise Time	t_r		—	12	—	ns
	Turn-On Time	t_{on}		—	20	—	
	Fall Time	t_f		—	100	—	
	Turn-Off Time	t_{off}		$V_{IN} : t_r, t_f < 5\text{ ns},$ $Duty \leq 1\%, t_w = 10\ \mu\text{s}$	—	250	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \doteq -24\text{ V}, V_{GS} = -10\text{ V},$ $I_D = -10\text{ A}$	—	52	—	nC
Gate-Source Charge		Q_{gs}		—	38	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	14	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	-10	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	-40	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = -10\text{ A}, V_{GS} = 0\text{ V}$	—	—	1.2	V

MARKING

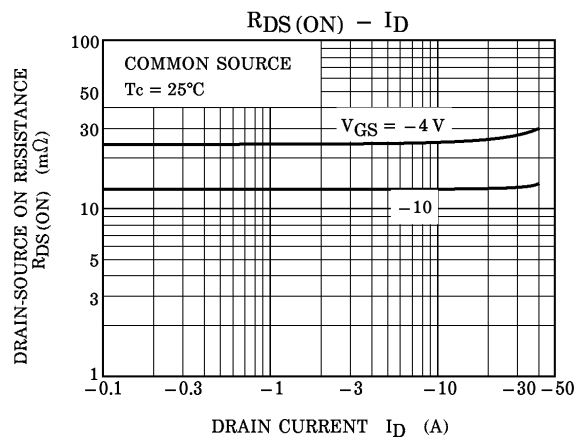
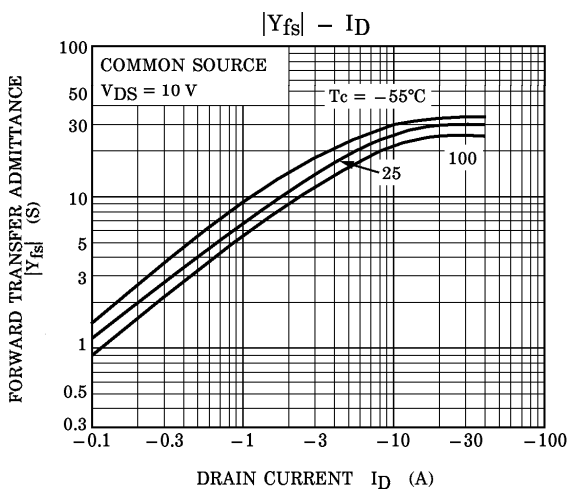
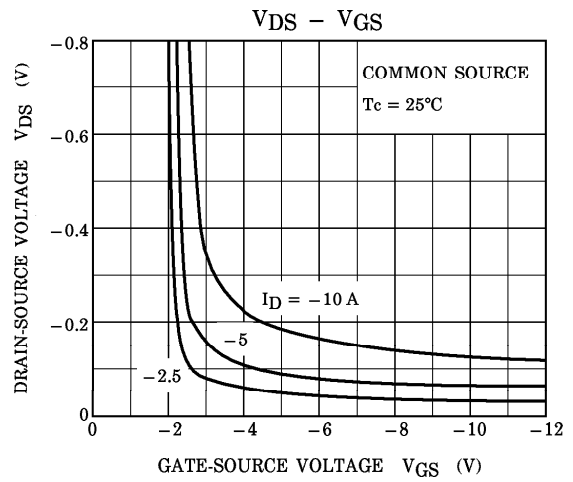
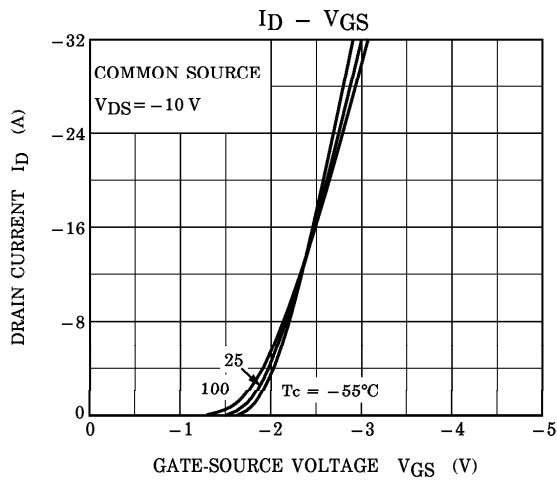
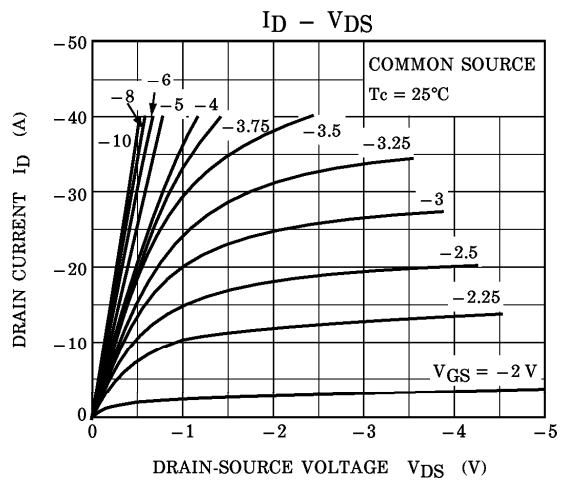
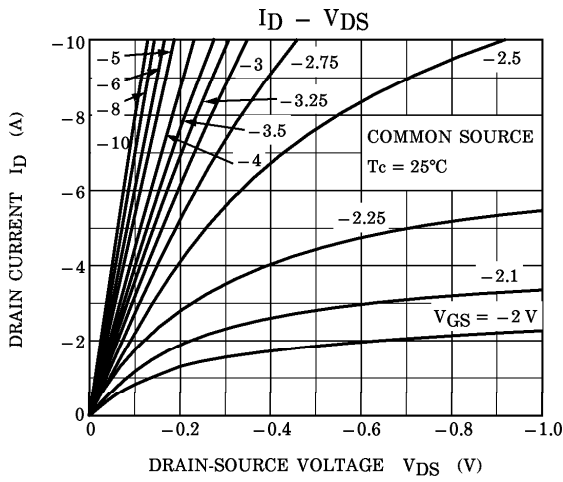


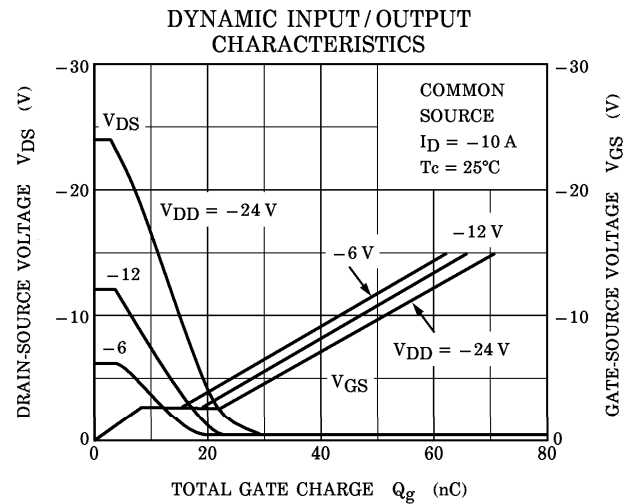
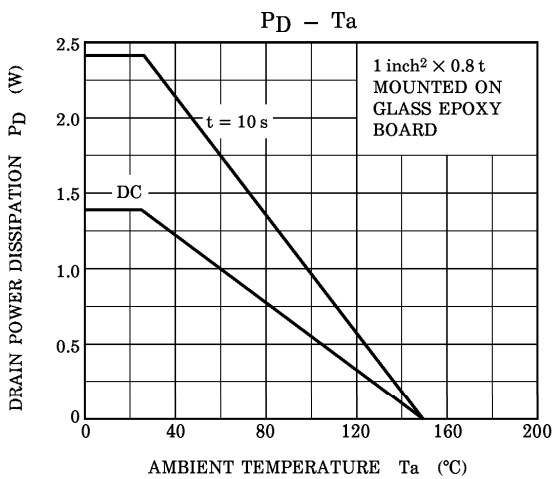
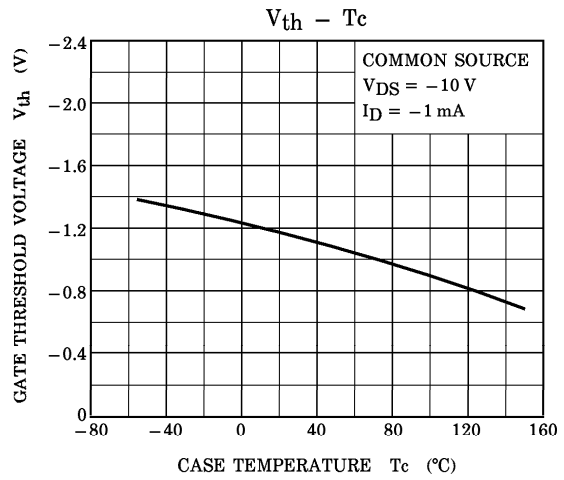
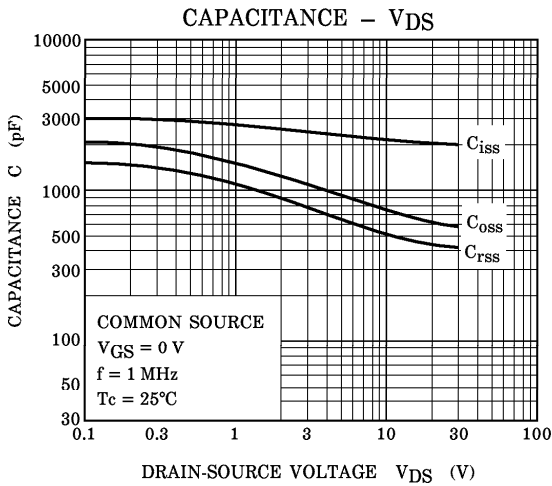
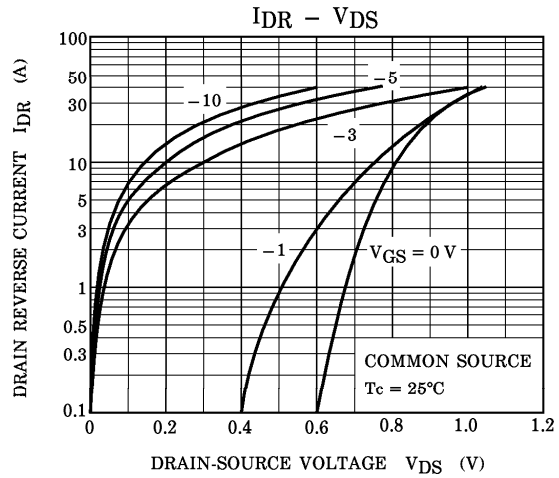
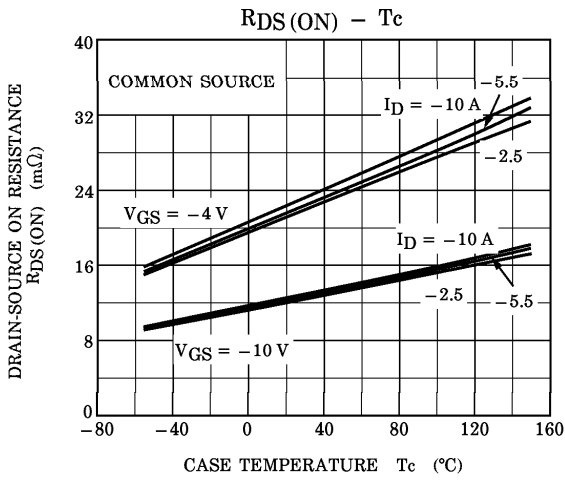
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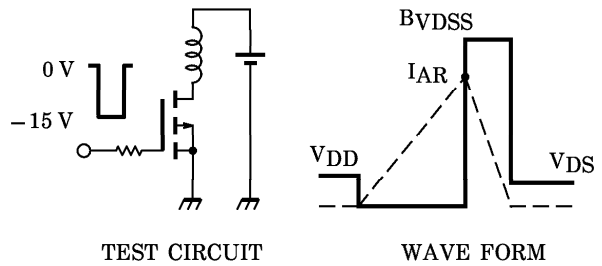
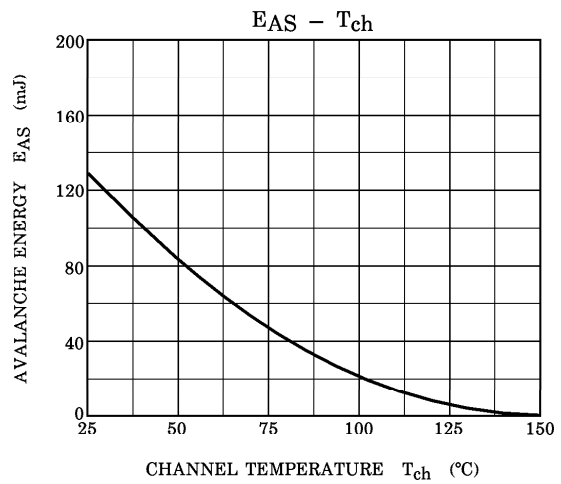
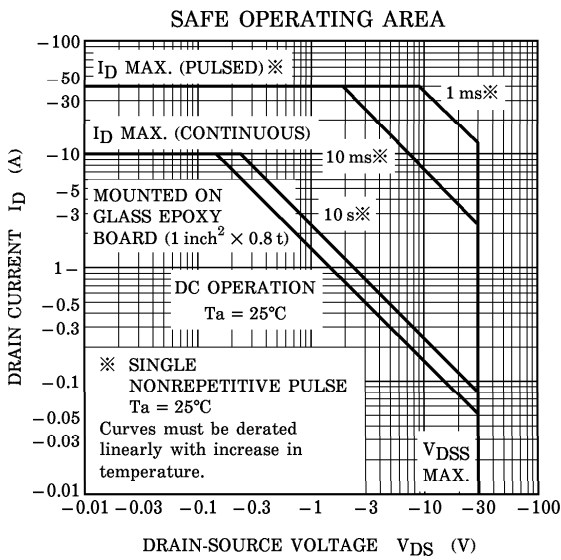
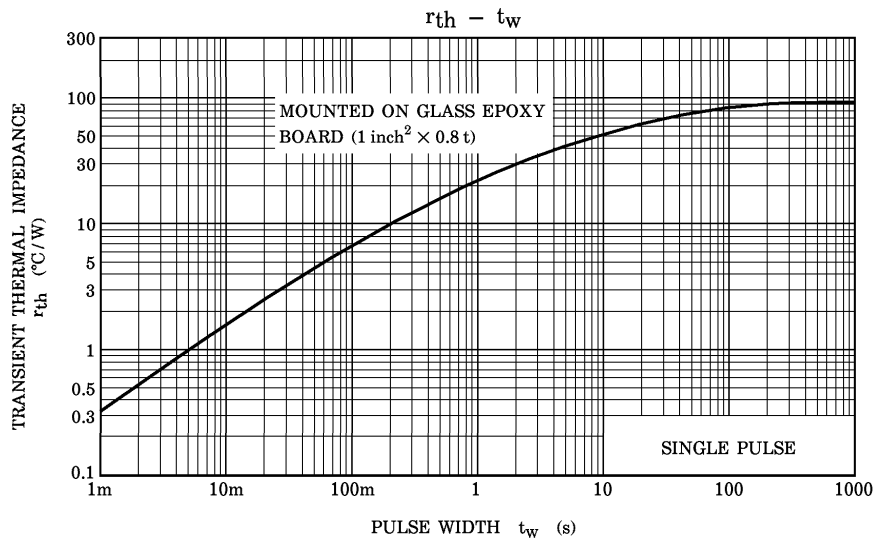
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak $I_{AR} = -10 \text{ A}$, $R_G = 25 \Omega$, $V_{DD} = -24 \text{ V}$, $L = 1.0 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$